

1. Material Substrate GaAlAs (N Type) Removed
 Epitaxial Layer GaAlAs (P/N Type)

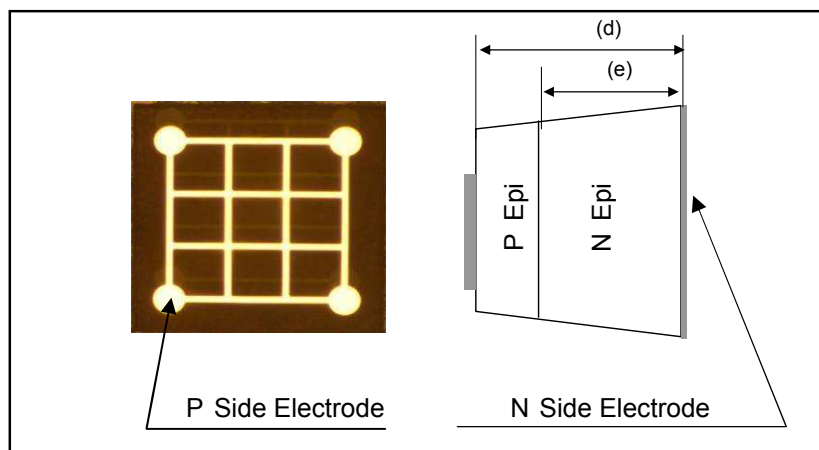
2. Electrode N(Cathode) Side Gold Alloy
 P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10mA
	$V_{F(2)}$			1.6	V	IF=250mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O		13.0		mW	IF=250mA
Wavelength	λ_P	840	850	855	nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	T_r		22.0		ns	
Fall Time	T_f		13		ns	

※ Note : LED chip is mounted on TO-18 gold header without resin coating.

4. Mechanical Data (a) Emission Area ----- 39.0mil x 39.0mil
 (b) Bottom Area ----- 39.4mil x 39.4mil
 (c) Bonding Pad ----- 120um
 (d) Chip Thickness ----- 7mil
 (e) Junction Height ----- 6.3mil



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